

EAST Search History

| Ref # | Hits | Search Query | DBs | Default Operator | Plurals | Time Stamp |
|-------|------|--|---|------------------|---------|---------------------|
| L1 | 498 | odte near3 semiconductor and detector | US-PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/08/31 10:29 |
| L2 | 161 | odte near3 semiconductor near6 detector | US-PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/08/31 10:30 |
| L5 | 0 | omos and intergated and (light adj emitting light \$1emitting) adj (device element diode) and common adj electrode | US-PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/08/31 10:46 |
| L6 | 201 | omos and integrated and (light adj emitting light \$1emitting) adj (device element diode) and common adj electrode | US-PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/08/31 10:46 |
| L7 | 91 | omos and integrated and (light adj emitting light \$1emitting) adj (device element diode) and common adj electrode and @ad< "20021224" | US-PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/08/31 10:47 |

| | | | | | | |
|-----|---------|--|---|----|----|---------------------|
| L8 | 13 | (257/8\$1.ccls. 257/9\$1.ccls. 257/10\$1.ccls.) and integrated adj circuit and cmos and common adj electrode | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/08/31 11:35 |
| L9 | 1 | (257/8\$1.ccls. 257/9\$1.ccls. 257/10\$1.ccls.) and integrated adj circuit and cmos and common adj electrode and print | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/08/31 12:07 |
| L10 | 18 | (257/8\$1.ccls. 257/9\$1.ccls. 257/10\$1.ccls.) and integrated adj circuit and common adj electrode and print | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/08/31 12:07 |
| L11 | 2696841 | (257/8\$1.ccls. 257/9\$1.ccls. 257/10\$1.ccls.) and integrated adj circuit and common adj electrode and print adh head | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/08/31 12:08 |
| L12 | 12 | (257/8\$1.ccls. 257/9\$1.ccls. 257/10\$1.ccls.) and integrated adj circuit and common adj electrode and print adj head | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/08/31 12:08 |
| L13 | 3 | "743104".ap. | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/08/31 12:40 |

| | | | | | | |
|-----|------|---|---|----|----|---------------------|
| L14 | 1 | (US-20040135157-\$.)\$.did. | US-PGPUB | OR | ON | 2008/08/31 12:41 |
| L16 | 1 | (US-20040135157-\$.)\$.did. | US-PGPUB | OR | ON | 2008/08/31 12:41 |
| L17 | 1 | 16 and (planari?e\$1 planari?ing) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/08/31 12:42 |
| L18 | 1557 | (planari?e\$1 planari?ing) near3 (region layer) near20 (depositing deposit forming) near20 metal | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/08/31 13:15 |
| L19 | 0 | (planari?e\$1 planari?ing) near3 (region layer) near20 (depositing deposit forming) near20 metal and interdielectric near4 (planarizing planarize planarization) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/08/31 13:16 |
| L20 | 8 | (planari?e\$1 planari?ing) near3 (region layer) near20 (depositing deposit forming) near20 metal and interdielectric | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/08/31 13:16 |
| L21 | 5704 | (planari?e\$1 planari?ing) near3 method.ti,ab,clm. | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/08/31 13:25 |

| | | | | | | |
|-----|-----|--|---|----|----|---------------------|
| L22 | 0 | (planari?e\$1 planari?ing) near3 method.ti,ab,clm. and planari?ing near4 dielectric and planari?ing near4 metal | US-PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/08/31 13:26 |
| L23 | 125 | (planari?e\$1 planari?ing) near3 method.ti,ab,clm. and planari?ing near4 dielectric and planari?ing near4 metal | US-PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/08/31 13:26 |
| L24 | 35 | (planari?e\$1 planari?ing) near3 method.ti,ab,clm. and planari?ing near4 dielectric and planari?ing near4 metal and barrier and @ad<"20021224" | US-PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/08/31 13:39 |
| L25 | 86 | barrier adj (layer film) and cmos and plurality near2 (light\$1emitting light adj emitting) | US-PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/08/31 13:48 |
| L26 | 2 | metal adj barrier adj (layer film) and plurality near2 (light\$1emitting light adj emitting) | US-PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/08/31 13:50 |
| L27 | 13 | barrier adj (layer film) near10 (common adj electrode) and (light\$1emitting light adj emitting) | US-PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/08/31 13:52 |

| | | | | | | |
|-----|-------|--|---|----|-----|---------------------|
| L28 | 2812 | 257/79 | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/08/31 15:44 |
| L29 | 13821 | ((257/79) or (257/88) or (257/93) or (257/98) or (257/99) or (257/499) or (257/501) or (257/678) or (257/905) or (257/906) or (257/911)).OQLS | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2008/08/31 15:46 |
| L30 | 1267 | 29 and (combined adj2 apparatus integrated adj circuit IC) and (silicon si) near2 substrate and (planari?e\$1 planari?ing planari?ation) and thin adj film and metal adj (layer film) and light\$1emitting and inorganic near3 compound and edge\$1 near3 (extend extending) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/08/31 15:49 |
| L31 | 0 | 29 and (combined adj2 apparatus integrated adj circuit IC) and (silicon si) near2 substrate and (planari?e\$1 planari?ing planari?ation) and thin adj film and metal adj (layer film) and light\$1emitting and inorganic near3 compound and edge\$1 near3 (extend extending) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/08/31 15:50 |
| L32 | 0 | ((ogihara).in. (fujiiwara).in. (sakuta).in. (abiko).in. (oki).as.) and (combined adj2 apparatus integrated adj circuit IC) and (silicon si) near2 substrate and (planari?e\$1 planari?ing planari?ation) and thin adj film and metal adj (layer film) and light\$1emitting and inorganic near3 compound and edge\$1 near3 (extend extending) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/08/31 15:51 |
| S1 | 4 | "743104".ap. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/06/12 13:38 |

| | | | | | | |
|-----|-----|---|---|----|-----|---------------------|
| S2 | 1 | (US-20040135157-\$).did. | US-PGPUB | OR | OFF | 2005/05/24 11:53 |
| S3 | 0 | jp-60206889\$-\$\$.did. | US-PGPUB | OR | OFF | 2005/05/24 11:54 |
| S4 | 1 | jp-60206889\$-\$\$.did. | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/05/24 11:58 |
| S5 | 2 | jp-10063807\$-\$\$.did. | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/05/24 11:58 |
| S6 | 152 | (257/93).CCLS. | US-PGPUB; USPAT | OR | OFF | 2005/06/11 19:50 |
| S7 | 209 | (257/501).CCLS. | US-PGPUB; USPAT | OR | OFF | 2005/06/11 19:50 |
| S8 | 360 | S6 S7 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/06/11 19:51 |
| S9 | 127 | S8 and (light adj emitting light-emitting) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/06/11 19:51 |
| S10 | 1 | S8 and (light adj emitting light-emitting) and (("without" "no") adj wire adj bond\$3) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/11 19:54 |

| | | | | | | |
|-----|------|--|---|----|-----|---------------------|
| S11 | 127 | S8 and (light adj emitting light-emitting) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/11 19:54 |
| S12 | 34 | S8 and (light adj emitting light-emitting) and planar \$5 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/11 19:54 |
| S13 | 14 | (US-6773943-\$ or US-6692845-\$ or US-6472718-\$ or US-6403985-\$ or US-6339233-\$ or US-6114715-\$ or US-5955747-\$ or US-5866922-\$ or US- 5663581-\$ or US-5115284-\$ or US-4984035-\$ or US-4956683-\$ or US-4335501-\$ or US-T979005-\$). did. | USPAT | OR | OFF | 2005/06/11 20:11 |
| S14 | 4 | S13 and print\$3 | US-PGPUB; USPAT | OR | OFF | 2005/06/11 20:33 |
| S15 | 5349 | ((257/79) or (257/88) or (257/93) or (257/99) or (257/499) or (257/501) or (257/678) or (257/687)). CCLS. | US-PGPUB; USPAT | OR | OFF | 2005/06/12 20:40 |
| S16 | 1 | S15 and monolithic and substrate near6 integrated adj circuit and planariz\$5 and (LED light-emitting light adj emitting laser adj diode) near2 array and thin adj2 film | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/06/11 20:39 |
| S17 | 2 | S15 and substrate near6 integrated adj circuit and planariz\$5 and (LED light-emitting light adj emitting laser adj diode) near2 array and thin adj2 film | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/06/11 20:43 |

| | | | | | | |
|-----|-----|--|---|----|-----|---------------------|
| S18 | 0 | S15 and monolithic and planariz\$5 and (LED light-emitting light adj emitting laser adj diode) near2 array and thin adj2 film | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/06/11 20:43 |
| S19 | 3 | S15 and monolithic and planariz\$5 and (LED light-emitting light adj emitting laser adj diode) near2 array and thin adj2 film | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/06/11 20:45 |
| S20 | 3 | S15 and integrated adj circuit near6 substrate and planariz\$5 and (LED light-emitting light adj emitting laser adj diode) near2 array and thin adj2 film | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/06/11 20:46 |
| S21 | 2 | S15 and integrated adj circuit near6 (semiconductor silicon) near4 substrate and planariz\$5 and (LED light-emitting light adj emitting laser adj diode) near2 array and thin adj2 film | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/06/11 20:47 |
| S22 | 2 | S15 and (IC integrated adj circuit) near6 (semiconductor silicon) near4 substrate and planariz\$5 and (LED light-emitting light adj emitting laser adj diode) near2 array and thin adj2 film | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/06/11 20:48 |
| S23 | 17 | (IC integrated adj circuit) near6 (semiconductor silicon) near4 substrate and planariz\$5 and (LED light-emitting light adj emitting laser adj diode) near2 array and thin adj2 film | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/06/11 20:55 |
| S24 | 154 | (IC integrated adj circuit) near6 (semiconductor silicon) near4 substrate and planariz\$5 and (LED light-emitting light adj emitting laser adj diode) and thin adj2 film | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/06/11 21:04 |

| | | | | | | |
|-----|------|--|---|----|-----|---------------------|
| S25 | 2 | ("5055907").PN. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/06/11 21:26 |
| S26 | 2 | ("4755866").PN. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/06/11 21:30 |
| S27 | 6922 | (light-emitting light adj emitting LED laser diode) adj array and (integrated adj circuit\$2 IC monolithic \$4) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/11 21:31 |
| S28 | 378 | (light-emitting light adj emitting LED laser diode) adj array and (integrated adj circuit\$2 IC monolithic \$4) and planariz\$5 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/11 21:38 |
| S29 | 189 | (light-emitting light adj emitting LED laser adj diode) adj array and (integrated adj circuit\$2 IC monolithic\$4) and planariz\$5 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/11 23:22 |
| S30 | 249 | semi-insulating adj substrate.ti. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/11 23:23 |
| S31 | 249 | semi-insulating adj substrate.ti. and semi-insulating | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/11 23:27 |

| | | | | | | |
|-----|------|--|---|----|----|---------------------|
| S32 | 3 | semi-insulating adj substrate.ti. and semi-insulating near6 defined | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/11 23:33 |
| S33 | 0 | (silicon semiconductor semi-insulating) adj substrate near4 "having" near4 (driver integrated) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/11 23:35 |
| S34 | 0 | (silicon semiconductor semi-insulating) adj substrate near4 "wherein" near4 (driver integrated) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/11 23:35 |
| S35 | 0 | (silicon semiconductor semi-insulating) adj substrate near10 "wherein" near4 (driver integrated IC) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/11 23:36 |
| S36 | 0 | (silicon semiconductor semi-insulating) adj substrate near10 "wherein" near10 (driver integrated IC) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/11 23:36 |
| S37 | 1481 | (silicon semiconductor semi-insulating) adj substrate near10 ("in which" "wherein" "having" "within") near10 (driver integrated IC) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/11 23:36 |
| S38 | 72 | (silicon semiconductor semi-insulating) adj substrate near10 ("in which" "wherein" "having" "within") near10 (driver integrated IC) and planariz \$5 and (LED light-emitting light adj emitting laser adj diode) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/11 23:51 |

| | | | | | | |
|-----|------|---|---|----|-----|---------------------|
| S39 | 4756 | (silicon semiconductor) adj substrate and thin adj2 film and passivation and (integrated adj circuit IC) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/11 23:52 |
| S40 | 3231 | (silicon semiconductor) adj substrate and thin adj2 film and passivation and (integrated adj circuit IC) and "257"/\$7.ccls. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/11 23:53 |
| S41 | 444 | (silicon semiconductor) adj substrate and thin adj2 film and passivation adj (layer film) near6 substrate and (integrated adj circuit IC) and "257"/\$7.ccls. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/11 23:56 |
| S42 | 317 | (silicon semiconductor) adj substrate and thin adj2 film and passivation adj (layer film) near6 substrate and (integrated adj circuit IC) and "257"/\$7.ccls. | USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/12 00:02 |
| S43 | 54 | (silicon semiconductor) adj substrate and thin adj2 film and planariz\$5 adj (layer film) near6 substrate and (integrated adj circuit IC) and "257"/\$7.ccls. | USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/12 00:02 |
| S44 | 2 | "5492851".pn. and semiconductor | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/06/12 15:03 |
| S45 | 2 | "4902637".pn. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/06/12 16:20 |

| | | | | | | |
|-----|----|---|---|----|-----|---------------------|
| S46 | 0 | (integrated adj circuit adj layer IC adj layer) and (planari?ation planari?e) and (light-emitting light adj emitting diode) adj array | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/06/12 15:11 |
| S47 | 0 | (integrated adj circuit adj layer IC adj layer) and (planari?ation planari?e) and (thin adj2 film light-emitting light adj emitting diode) adj array | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/06/12 15:12 |
| S48 | 79 | (integrated adj circuit adj layer IC adj layer) and (planari?ation planari?e) and (thin adj2 film light-emitting light adj emitting diode) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/06/12 15:22 |
| S49 | 15 | (US-20050087817-\$ or US-20040155302-\$ or US-20040155301-\$ or US-20040016976-\$ or US-20040012053-\$ or US-20040007746-\$ or US-20030067043-\$).did. or (US-6903427-\$ or US-6861715-\$ or US-6812488-\$ or US-6717222-\$ or US-6706546-\$ or US-6690845-\$ or US-6684007-\$ or US-6611635-\$).did. | US-PGPUB; USPAT | OR | OFF | 2005/06/12 15:22 |
| S50 | 4 | S49 and thin adj film near5 planariz\$5 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/06/12 15:57 |
| S51 | 0 | S49 and thin adj film near5 planariz\$5 and integrated adj circuit adj layer | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/06/12 15:25 |

| | | | | | | |
|-----|----|---|---|----|-----|---------------------|
| S52 | 4 | S49 and thin adj film near5 planariz\$5 and (IC adj layer integrated adj circuit adj layer) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/12 15:28 |
| S53 | 4 | S49 and thin adj film near5 planariz\$5 and (IC adj layer integrated adj circuit adj layer) and thin adj film adj device | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/12 15:45 |
| S54 | 4 | S49 and thin adj film near5 planariz\$5 and (IC adj layer integrated adj circuit adj layer) and thin adj film adj device and IC adj chip adj layer | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/12 15:50 |
| S55 | 0 | S49 and thin adj film near5 planariz\$5 and (IC adj layer integrated adj circuit adj layer) and thin adj film adj device and IC adj chip adj layer and vcsl adj layer | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/12 15:51 |
| S56 | 4 | S49 and thin adj film near5 planariz\$5 and (IC adj layer integrated adj circuit adj layer) and thin adj film adj device and IC adj chip adj layer and device adj layer | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/12 15:52 |
| S57 | 4 | S49 and thin adj film near5 planariz\$5 and (IC adj layer integrated adj circuit adj layer) and thin adj film adj device and IC adj chip adj layer and device adj layer and (planari?e planari?ation) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/12 15:53 |
| S58 | 15 | S49 and planariz\$5 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/06/12 15:58 |

| | | | | | | |
|-----|----|--|---|----|-----|---------------------|
| S59 | 0 | S49 and planariz\$5 and integrated adj circuit adj layer | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/06/12 15:58 |
| S60 | 15 | S49 and planariz\$5 and (IC integrated adj circuit) adj2 layer | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/12 15:58 |
| S61 | 15 | S49 and planariz\$5 and (IC integrated adj circuit) adj2 layer and thin adj film | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/12 16:00 |
| S62 | 4 | S49 and planariz\$5 and (IC integrated adj circuit) adj2 layer and thin adj film and (light-emitting light adj emitting vcsel) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/12 16:00 |
| S63 | 4 | S49 and planariz\$5 and (IC integrated adj circuit) adj2 layer and thin adj film and (light-emitting light adj emitting vcsel piezoelectric hall) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/12 16:01 |
| S64 | 4 | S49 and planariz\$5 and (IC integrated adj circuit) adj2 layer and thin adj film and (light-emitting light adj emitting vcsel piezoelectric hall laser adj diode photodetect\$3 photodiode) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/12 16:01 |
| S65 | 15 | IC adj layer near6 stack\$3 and (planari?ation planari?e) and (EO LED light-emitting light adj emitting laser diode vcsel photodiode photodetect \$3 hall adj sensor piezo-electric piezoelectric) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/12 17:24 |

| | | | | | | |
|-----|------|---|---|----|----|---------------------|
| S66 | 29 | cd-rom near4 diode | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/12 18:37 |
| S67 | 5991 | memory adj device and memory adj cell adj array and ((semiconductor silicon) adj substrate) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/12 17:25 |
| S68 | 2403 | memory adj device and memory adj cell adj array.ti, ab,clm. and ((semiconductor silicon) adj substrate) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/12 17:25 |
| S69 | 1206 | memory adj device and memory adj cell adj array.ti, ab,clm. and ((semiconductor silicon) adj substrate). ti,ab,clm. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/12 17:25 |
| S70 | 687 | memory adj device and memory adj cell adj array.ti, ab,clm. and ((semiconductor silicon) adj substrate). ti,ab,clm. | USPAT | OR | ON | 2005/06/12 17:26 |
| S71 | 0 | memory adj device and memory adj cell adj array.ti, ab,clm. and ((GaAs) adj substrate).ti,ab,clm. | USPAT | OR | ON | 2005/06/12 17:26 |
| S72 | 0 | memory adj device and memory adj cell adj array.ti, ab,clm. and ((GaAs) adj substrate).ti,ab,clm. | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT | OR | ON | 2005/06/12 17:26 |
| S73 | 0 | memory adj device and memory adj cell adj array.ti, ab,clm. and (GaAs AlGaAs) adj substrate.ti,ab,clm. | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT | OR | ON | 2005/06/12 17:27 |

| | | | | | | |
|-----|-------|--|---|----|----|---------------------|
| S74 | 0 | memory adj device and memory adj cell adj array.ti, ab,clm. and (SiGe SiC GaAs AlGaAs) adj substrate.ti, ab,clm. | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT | OR | ON | 2005/06/12 17:27 |
| S75 | 0 | memory adj device and memory adj cell adj array and (SiGe SiC GaAs AlGaAs) adj substrate.ti,ab,clm. | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT | OR | ON | 2005/06/12 17:27 |
| S76 | 45 | memory adj device and (SiGe SiC GaAs AlGaAs) adj substrate.ti,ab,clm. | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT | OR | ON | 2005/06/12 17:33 |
| S77 | 5 | memory adj device and (SiC) adj substrate.ti,ab, clm. | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT | OR | ON | 2005/06/12 17:34 |
| S78 | 39 | memory adj device and (GaAs) adj substrate.ti,ab, clm. | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT | OR | ON | 2005/06/12 17:34 |
| S79 | 12 | config-dielectric | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/12 20:01 |
| S80 | 8 | source near6 common adj ground and memory adj array.ti. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/12 20:11 |
| S81 | 31389 | CD-ROM and Dvd | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/12 20:12 |

| | | | | | | |
|-----|------|--|---|----|-----|---------------------|
| S82 | 2 | CD-ROM and Dvd and memory adj array and laser adj diode | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/12 20:13 |
| S83 | 2 | "5696714".pn. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/12 20:13 |
| S84 | 5611 | ((257/79) or (257/88) or (257/93) or (257/99) or (257/499) or (257/501) or (257/678) or (257/687) or (257/905) or (257/906) or (257/911)).CCLS. | US-PGPUB; USPAT | OR | OFF | 2005/06/12 20:40 |
| S85 | 0 | S84 and (planari?ation planari?e) and (Si silicon semiconductor) adj thin adj film and (integrated adj circuit IC) adj2 (layer) and (light-emitting light adj emitting laser adj diode photodiode photodetect\$3 hall adj sensor) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/06/12 20:42 |
| S86 | 4649 | integrated adj circuit and (semiconductor silicon gallium adj arsenide gallium adj nitride gaas gan si) near2 substrate and (planarise planarising planarisation planarize planarization planarizing) and thin adj film | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/02/23 15:59 |
| S87 | 806 | integrated adj circuit and (semiconductor silicon gallium adj arsenide gallium adj nitride gaas gan si) near2 substrate and (planarise planarising planarisation planarize planarization planarizing) near4 (thin adj film film) and (planarise planarising planarisation planarize planarization planarizing) near4 (layer inter-layer) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/02/23 16:01 |

| | | | | | | |
|-----|---|--|---|----|----|---------------------|
| S88 | 6 | integrated adj circuit and (semiconductor silicon gallium adj arsenide gallium adj nitride gaas gan si) near2 substrate and (planarise planarising planarisation planarize planarization planarizing) near4 (thin adj film film) and (planarise planarising planarisation planarize planarization planarizing) near4 (layer inter-layer) and electrode and oled | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/02/23 16:03 |
| S89 | 2 | integrated adj circuit and (semiconductor silicon gallium adj arsenide gallium adj nitride gaas gan si) near2 substrate and (planarise planarising planarisation planarize planarization planarizing) near4 (thin adj film film) and (planarise planarising planarisation planarize planarization planarizing) near4 (layer inter-layer) and electrode and oled and @ad<"20021225" | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/02/23 16:04 |
| S90 | 0 | integrated adj circuit and (semiconductor silicon gallium adj arsenide gallium adj nitride gaas gan si) near2 substrate and (planarise planarising planarisation planarize planarization planarizing) near4 (thin adj film film) and (planarise planarising planarisation planarize planarization planarizing) near4 (layer inter-layer) and electrode and (electroluminescent adj layer) and @ad<"20021225" | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/02/23 16:05 |
| S91 | 0 | integrated adj circuit and (semiconductor silicon gallium adj arsenide gallium adj nitride gaas gan si) near2 substrate and (planarise planarising planarisation planarize planarization planarizing) near4 (thin adj film film) and (planarise planarising planarisation planarize planarization planarizing) near4 (layer inter-layer) and electrode and (electroluminescent adj layer) and @ad<"20021225" | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/02/23 16:05 |

| | | | | | | |
|-----|------|--|---|----|----|---------------------|
| S92 | 9 | integrated adj circuit and (semiconductor silicon gallium adj arsenide gallium adj nitride gaas gan si) near2 substrate and (planarise planarising planarisation planarize planarization planarizing) near4 (thin adj film film) and (planarise planarising planarisation planarize planarization planarizing) near4 (layer inter-layer) and electrode and light-emitting and @ad< "20021225" | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/02/23 16:06 |
| S93 | 12 | integrated adj circuit and (semiconductor silicon gallium adj arsenide gallium adj nitride gaas gan si) near2 substrate and (planarise planarising planarisation planarize planarization planarizing) near4 (thin adj film film) and (planarise planarising planarisation planarize planarization planarizing) near4 (layer inter-layer) and electrode and (light adj emitting light-emitting) and @ad< "20021225" | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/02/23 16:06 |
| S94 | 1614 | (planari?e planari?ed palanari?ation planari?ing) near2 (region layer) and (planari?e planari?ed palanari?ation planari?ing) near2 (film) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/02/23 17:07 |
| S95 | 1097 | (planari?e planari?ed palanari?ation planari?ing) near2 (region layer) and (planari?e planari?ed palanari?ation planari?ing) near2 (film) and substrate near1 (semiconduct\$3 silicon si gan gaas gallium adj arseinde gallium adj nitride) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/02/23 17:08 |
| S96 | 1098 | (planari?e planari?ed palanari?ation planari?ing) near2 (region layer) and (planari?e planari?ed palanari?ation planari?ing) near2 (film) and substrate near1 (semiconduct\$3 silicon si gan gaas gallium adj arsenide gallium adj nitride) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/02/23 17:08 |

| | | | | | | |
|------|-----|--|---|----|----|---------------------|
| S97 | 534 | (planari?e planari?ed palanari?ation planari?ing) near2 (region layer) and (planari?e planari?ed palanari?ation planari?ing) near2 (film) and substrate near1 (semiconduct\$3 silicon si gan gaas gallium adj arsenide gallium adj nitride) and (integrated adj circuit IC) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/02/23 17:09 |
| S98 | 287 | (planari?e planari?ed palanari?ation planari?ing) near2 (region layer) and (planari?e planari?ed palanari?ation planari?ing) near2 (film) and substrate near1 (semiconduct\$3 silicon si gan gaas gallium adj arsenide gallium adj nitride) and (integrated adj circuit IC) and thin adj film | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/02/23 17:10 |
| S99 | 196 | (planari?e planari?ed palanari?ation planari?ing) near2 (region layer) and (planari?e planari?ed palanari?ation planari?ing) near2 (film) and substrate near1 (semiconduct\$3 silicon si gan gaas gallium adj arsenide gallium adj nitride) and (integrated adj circuit IC) and thin adj film and @ad<"20021225" | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/02/23 17:10 |
| S100 | 15 | (planari?e planari?ed palanari?ation planari?ing) near2 (region layer) and (planari?e planari?ed palanari?ation planari?ing) near2 (film) and substrate near1 (semiconduct\$3 silicon si gan gaas gallium adj arsenide gallium adj nitride) and (integrated adj circuit IC) and thin adj film and @ad<"20021225" and (light-emitting light adj emitting) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/02/23 17:13 |
| S101 | 22 | (planari?e planari?ed palanari?ation planari?ing) near2 (region layer) and (planari?e planari?ed palanari?ation planari?ing) near2 (film) and substrate near1 (semiconduct\$3 silicon si gan gaas gallium adj arsenide gallium adj nitride) and (integrated adj circuit IC) and thin adj film and @ad<"20021225" and (light-emitting light adj emitting) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/02/23 17:16 |

| | | | | | | |
|------|-----|---|---|----|----|---------------------|
| S102 | 32 | (planari?e planari?ed planari?ation planari?ing planar) near2 (region layer) and (planari?e planari?ed planari?ation planari?ing planar) near2 (film) and substrate near1 (semiconduct\$3 silicon si gan gaas gallium adj arsenide gallium adj nitride) and (integrated adj circuit IC) and thin adj film and @ad<"20021225" and (light-emitting light adj emitting) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/02/23 17:37 |
| S103 | 13 | (first second) near1 (planari?e planari?ed planari?ation planari?ing planar) near2 (region layer film) and substrate near1 (semiconduct\$3 silicon si gan gaas gallium adj arsenide gallium adj nitride) and (integrated adj circuit IC) and thin adj film and @ad<"20021225" and (light-emitting light adj emitting) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/02/23 17:41 |
| S104 | 210 | (first second) near1 (planari?e planari?ed planari?ation planari?ing planar) near2 (region layer film) and substrate near1 (semiconduct\$3 silicon si gan gaas gallium adj arsenide gallium adj nitride) and (integrated adj circuit IC) and thin adj film and @ad<"20021225" | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/02/23 17:45 |
| S105 | 62 | first near2 (planari?e planari?ed planari?ation planari?ing planar) near2 (region layer film) and second near2 (planari?e planari?ed planari?ation planari?ing planar) near2 (region layer film) and substrate near1 (semiconduct\$3 silicon si gan gaas gallium adj arsenide gallium adj nitride) and (integrated adj circuit IC) and thin adj film and @ad<"20021225" | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/02/23 17:47 |

| | | | | | | |
|------|----|--|---|----|----|---------------------|
| S106 | 2 | first near2 (planari?e planari?ed planari?ation planari?ing planar) near2 (region layer film) and second near2 (planari?e planari?ed planari?ation planari?ing planar) near2 (region layer film) and substrate near1 (semiconduct\$3 silicon si gan gaas gallium adj arsenide gallium adj nitride) and (integrated adj circuit IC) and thin adj film and @ad<"20021225" and (light-emitting light adj emitting) and thin adj film | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/02/23 17:48 |
| S107 | 2 | first near2 (planari?e planari?ed planari?ation planari?ing planar) near2 (region layer film) and second near2 (planari?e planari?ed planari?ation planari?ing planar) near2 (region layer film) and substrate near1 (semiconduct\$3 silicon si gan gaas gallium adj arsenide gallium adj nitride) and (integrated adj circuit IC) and thin adj film and @ad<"20021225" and (light-emitting light adj emitting) and (tft thin adj film oft) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/02/23 17:50 |
| S108 | 2 | first near2 (planari?e planari?ed planari?ation planari?ing planar) near2 (region layer film) and second near2 (planari?e planari?ed planari?ation planari?ing planar) near2 (region layer film) and substrate near1 (semiconduct\$3 silicon si gan gaas gallium adj arsenide gallium adj nitride) and (integrated adj circuit IC) and thin adj film and @ad<"20021225" and (light-emitting light adj emitting) and (tft thin adj film oft silicon-on-insulator "soi") | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/02/23 17:51 |
| S109 | 14 | first near2 (planari?e planari?ed planari?ation planari?ing planar) near2 (region layer film) and second near2 (planari?e planari?ed planari?ation planari?ing planar) near2 (region layer film) and (integrated adj circuit IC) and thin adj film and @ad<"20021225" and (light-emitting light adj emitting) and (tft thin adj film oft silicon-on-insulator "soi") | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/02/23 18:31 |

| | | | | | | |
|------|-----|---------------------|---|----|-----|---------------------|
| S110 | 2 | ("20030067043").PN. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2006/02/23 18:33 |
| S111 | 19 | "5492851" | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2006/02/23 18:34 |
| S112 | 2 | ("5492851").PN. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2006/02/23 18:34 |
| S113 | 2 | S112 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2006/02/23 18:42 |
| S114 | 2 | ("20050199924").PN. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2006/02/23 19:02 |
| S115 | 2 | ("20050052823").PN. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2006/02/23 19:13 |
| S116 | 509 | (257/752).COLS. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2006/02/23 19:38 |

| | | | | | | |
|------|-----|--|---|----|-----|---------------------|
| S117 | 22 | S116 and (thin adj film adj transistor tft oft) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2006/02/23 19:38 |
| S118 | 22 | S116 and (thin adj film adj transistor tft oft) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/02/23 19:40 |
| S119 | 19 | S116 and (thin adj film adj transistor tft oft) and (planar planari?e planari?ed planari?ation planari?) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/02/23 19:41 |
| S120 | 537 | (silicon-on-insulator "SOI") and driver and pixel and (planar planari?e planari?ed planari?ation planari? ing) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/02/24 08:16 |
| S121 | 0 | (silicon-on-insulator "SOI") and driver and pixel and (planar planari?e planari?ed planari?ation planari? ing) and intergated adj circuit and (silicon semiconductor) near1 substrate and @ad<"20021225" | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/02/24 08:17 |
| S122 | 184 | (silicon-on-insulator "SOI") and driver and pixel and (planar planari?e planari?ed planari?ation planari? ing) and integrated adj circuit and (silicon semiconductor) near1 substrate and @ad<"20021225" | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/02/24 08:18 |
| S123 | 139 | (silicon-on-insulator "SOI") and driver and pixel and (planar planari?e planari?ed planari?ation planari? ing) and integrated adj circuit and (silicon semiconductor) near1 substrate and @ad<"20021225" | USPAT; EPO; JPO; IBM_TDB | OR | ON | 2006/02/24 08:26 |

| | | | | | | |
|------|------|---|---|----|-----|---------------------|
| S124 | 1 | (US-20040135157-\$).did. | US-PGPUB | OR | OFF | 2006/02/24 08:41 |
| S125 | 1 | S124 and raised adj layer | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2006/02/24 09:40 |
| S126 | 0 | zhang.in. and stacked near4 tft | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2006/02/24 09:41 |
| S127 | 0 | semiconductor adj energy.in. and stacked near4 tft | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2006/02/24 09:41 |
| S128 | 0 | semiconductor adj energy.in. and stack\$3 near4 tft | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/02/24 09:42 |
| S129 | 0 | semiconductor adj energy.in. and tft | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/02/24 09:42 |
| S130 | 5688 | semiconductor adj energy.as. and tft | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/02/24 09:42 |

| | | | | | | |
|------|-----|--|---|----|-----|---------------------|
| S131 | 21 | semiconductor adj energy.as. and tft near4 stack\$4 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/02/24 09:44 |
| S132 | 457 | tft near4 stack\$4 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/02/24 09:44 |
| S133 | 64 | tft near4 stack\$4.ti,ab,clm. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/02/24 10:38 |
| S134 | 28 | tft near4 stack\$4.ti,ab,clm. and (silicon semiconductor) near4 substrate | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/02/24 10:38 |
| S135 | 1 | (US-20040135157-\$.).did. | US-PGPUB | OR | OFF | 2006/02/24 15:03 |
| S136 | 9 | optical adj print adj head and (tft active adj matrix adj display) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/02/24 15:07 |
| S137 | 7 | optical adj print adj head and (active adj matrix) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/02/24 15:09 |

| | | | | | | |
|------|----|--|---|----|----|---------------------|
| S138 | 5 | optical adj print adj head and (active adj matrix) and print adj head and tft | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/02/24 15:09 |
| S139 | 0 | optical adj print adj head and (active adj matrix) and print adj head near20 tft | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/02/24 15:09 |
| S140 | 0 | optical adj print adj head and (active adj matrix) and print adj head same tft | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/02/24 15:09 |
| S141 | 7 | optical adj print adj head and (active adj matrix) and print adj head | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/02/24 15:12 |
| S142 | 48 | print adj head and ((active adj matrix) near20 tft) and print adj head | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/02/24 15:13 |
| S143 | 1 | print adj head and ((active adj matrix) near20 tft) near20 (print adj head) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/02/24 15:14 |

| | | | | | | |
|------|---|---|---|----|----|---------------------|
| S144 | 1 | print\$3 adj head and ((active adj matrix) near20 tft) near20 (print\$3 adj head) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/02/24 15:16 |
| S145 | 0 | print\$3 adj head and ((matrix adj2 display) near20 tft) near20 (print\$3 adj head) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/02/24 15:16 |
| S146 | 1 | print\$3 adj head and ((matrix) near20 tft) near20 (print\$3 adj head) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/02/24 15:28 |
| S147 | 0 | 09-045930\$-\$\$.did. | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/02/24 15:28 |
| S148 | 0 | *09045930*\$-\$\$.did. | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/02/24 15:28 |
| S149 | 2 | jp-09045930\$-\$\$.did. | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/02/24 19:43 |

| | | | | | | |
|------|----|---|---|----|-----|---------------------|
| S150 | 0 | "6255705".pn. and print\$3 | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/02/24 15:41 |
| S151 | 1 | (US-20040135157-\$).did. | US-PGPUB | OR | OFF | 2006/02/24 17:21 |
| S152 | 1 | S151 and common | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2006/02/24 17:21 |
| S153 | 1 | S151 and common | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/02/24 17:21 |
| S154 | 61 | (US-20030141504-\$ or US-20020163000-\$ or US-20040135157-\$ or US-20030067043-\$ or US-20020168856-\$ or US-20040012053-\$ or US-20040007746-\$ or US-20040130015-\$ or US-20040094770-\$ or US-20030102473-\$ or US-20040125197-\$ or US-20040166659-\$ or US-20030170934-\$ or US-20040089939-\$ or US-20050100279-\$ or US-20030133668-\$ or US-20040155302-\$ or US-20040155301-\$ or US-20050087817-\$ or US-20040016976-\$ or US-20020061040-\$).did. or (US-6828227-\$ or US-5492851-\$ or US-5031187-\$ or US-6692837-\$ or US-6476485-\$ or US-6307264-\$ or US-4902637-\$ or US-6876008-\$ or US-6773943-\$ or US-6692845-\$ or US-6472718-\$ or US-6403985-\$ or US-6339233-\$ or US-6114715-\$ or US-5955747-\$ or US-5866922-\$ or US-5663581-\$ or US-5115284-\$ or US-4984035-\$ or US-4956683-\$ or US-4335501-\$ or US-T979005-\$ or US-5055907-\$ or US- | US-PGPUB; USPAT; JPO; DERWENT | OR | OFF | 2006/02/24 17:24 |

| | | | | | | |
|------|----|--|---|----|-----|---------------------|
| | | 5789766-\$ or US-6410960-\$ or US-6903427-\$).did. or (US-6849877-\$ or US-6861715-\$ or US-6812488-\$ or US-6717222-\$ or US-6706546-\$ or US- 6690845-\$ or US-6684007-\$ or US-6611635-\$ or US-6222755-\$ or US-5696714-\$ or US-6380572-\$). did. or (JP-10063807-\$ or JP-61102767-\$).did. or (JP-10063807-\$).did. | | | | |
| S155 | 1 | S154 and common near2 (source drain gate) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2006/02/24 17:25 |
| S156 | 1 | S154 and gate adj line | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2006/02/24 18:04 |
| S157 | 40 | tft and active adj matrix and compound adj semiconductor near10 substrate | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2006/02/24 18:05 |
| S158 | 18 | tft and active adj matrix and compound adj semiconductor near1 substrate | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2006/02/24 18:15 |
| S159 | 0 | tft and active adj matrix and compound adj semiconductor near1 channel | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/02/24 18:16 |

| | | | | | | |
|------|----|---|---|----|-----|---------------------|
| S160 | 0 | tft and active adj matrix and (gan gaas compound adj semiconductor) near1 channel | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/02/24 18:16 |
| S161 | 14 | tft and (gan gaas compound adj semiconductor) near5 channel | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/02/24 18:17 |
| S162 | 2 | ("20030067043").PNL | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2006/02/24 19:43 |
| S163 | 7 | "734294".ap. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/02/25 13:52 |
| S164 | 2 | ("5838608").PNL | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2006/02/25 14:34 |
| S165 | 19 | "5492851" | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2006/02/25 14:34 |
| S166 | 2 | ("5492851").PNL | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2006/02/25 14:41 |

| | | | | | | |
|------|------|--|---|----|-----|---------------------|
| S167 | 0 | ("743294.ap.").PN. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2006/02/25 14:41 |
| S168 | 6 | "743294".ap. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2006/02/25 14:41 |
| S169 | 7 | "734294".ap. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2006/02/25 14:42 |
| S170 | 2 | "20040175887".pn. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2006/02/25 15:28 |
| S171 | 2 | ("20030067043").PN. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2006/02/25 16:03 |
| S172 | 8789 | ((257/79) or (257/93) or (257/88) or (257/99) or (257/499) or (257/501) or (257/678) or (257/687) or (257/905) or (257/906) or (257/911)).CCL.S. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2006/02/25 16:04 |
| S173 | 0 | S172 and planarized adj (layer region film).clm. and (integrated adj circuit IC).clm. and (semiconductor silicon gan gaas sige) near2 substrate.clm. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/02/25 16:06 |

| | | | | | | |
|------|---|---|---|----|-----|---------------------|
| S174 | 0 | S172 and planarized near4 (layer region film).clm. and (integrated adj circuit IC).clm. and (semiconductor silicon gan gaas sige) near2 substrate.clm. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/02/25 16:06 |
| S175 | 1 | S172 and planarized near4 (layer region film).ti.ab, clm. and (integrated adj circuit IC).ti.ab,clm. and (semiconductor silicon gan gaas sige) near2 substrate.ti.ab,clm. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/02/25 16:06 |
| S176 | 2 | ("6255705").PN. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2006/12/08 20:03 |
| S177 | 5 | "384014".ap. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2006/12/08 20:06 |
| S178 | 2 | ("20040173808").PN. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2006/12/08 20:06 |
| S179 | 8 | "561564" | DERWENT | OR | OFF | 2006/12/08 20:07 |
| S180 | 2 | ("20030067043").PN. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2006/12/09 00:10 |
| S181 | 1 | (US-20040135157-\$).did. | US-PGPUB | OR | OFF | 2007/05/26 00:19 |

| | | | | | | |
|------|----|---|---|----|-----|---------------------|
| S182 | 1 | (US-20040135157-\$).did. and rough\$4 | US-PGPUB | OR | ON | 2007/05/26 00:20 |
| S183 | 2 | ("6255705").PNL | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2007/05/26 00:21 |
| S184 | 1 | (US-20040135157-\$).did. | US-PGPUB | OR | OFF | 2007/05/26 16:00 |
| S186 | 1 | (US-20040135157-\$).did. | US-PGPUB | OR | OFF | 2007/05/26 16:01 |
| S187 | 1 | S186 and rough\$3 | US-PGPUB | OR | OFF | 2007/05/26 16:32 |
| S188 | 1 | S186 and rough\$3 and thin adj2 film | US-PGPUB | OR | OFF | 2007/05/26 16:49 |
| S189 | 1 | S186 and compound | US-PGPUB | OR | OFF | 2007/05/26 16:49 |
| S190 | 1 | S186 and epitaxial\$2 and thin and compound | US-PGPUB | OR | OFF | 2007/05/26 17:16 |
| S191 | 66 | (planari?ation planari?e planari?ed planari?ing).ti,ab, clm. and (integrated adj circuit IC adj chip).ti,ab, clm. and (light-emitting light adj emitting).ti,ab,clm. | US-PGPUB | OR | ON | 2007/05/26 17:19 |
| S192 | 22 | (planari?ation planari?e planari?ed planari?ing).ti,ab, clm. and (integrated adj circuit IC adj chip).ti,ab, clm. and (light-emitting light adj emitting).ti,ab,clm. and "257"/\$7.ccls. | US-PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/05/26 20:18 |
| S193 | 22 | (planari?ation planari?e planari?ed planari?ing).ti,ab, clm. and (integrated adj circuit IC adj chip).ti,ab, clm. and (light-emitting light adj emitting).ti,ab,clm. and "257"/\$7.ccls. | US-PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/05/26 20:26 |

| | | | | | | |
|------|----|---|---|----|----|---------------------|
| S194 | 22 | S193 and (planari?ation planari?e planari?ed planari?ing) and (integrated adj circuit IC adj chip) and (light-emitting light adj emitting) and "257"/\$7.ccls. | US-PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/05/26 20:24 |
| S195 | 1 | S193 and (planari?ation planari?e planari?ed planari?ing) and (integrated adj circuit IC adj chip) and (light-emitting light adj emitting) and "257"/\$7.ccls. and monitoring adj device | US-PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/05/26 20:25 |
| S196 | 43 | (planari?ation planari?e planari?ed planari?ing).ti,ab,clm. and (integrated adj circuit IC adj chip).ti,ab,clm. and (light-emitting light adj emitting) and "257"/\$7.ccls. | US-PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/05/26 20:36 |
| S197 | 4 | (planari?ation planari?e planari?ed planari?ing).ti,ab,clm. and (integrated adj circuit IC adj chip).ti,ab,clm. and (light-emitting light adj emitting) and (257/79.ccls. 257/8\$1.ccls. 257/9\$1.ccls. 257/100.ccls. 257/101.ccls. 257/102.ccls. 257/103.ccls.) | US-PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/05/26 20:37 |
| S198 | 13 | (planari?ation planari?e planari?ed planari?ing).ti,ab,clm. and (integrated adj circuit IC adj chip).ti,ab,clm. and (light-emitting light adj emitting laser) and (257/79.ccls. 257/8\$1.ccls. 257/9\$1.ccls. 257/100.ccls. 257/101.ccls. 257/102.ccls. 257/103.ccls. "372"/\$7.ccls.) | US-PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/05/26 20:41 |
| S199 | 72 | (planari?ation planari?e planari?ed planari?ing).ti,ab,clm. and (integrated adj circuit IC adj chip).ti,ab,clm. and (light-emitting light adj emitting laser) and (thin adj film adj transistor 257/79.ccls. 257/8\$1.ccls. 257/9\$1.ccls. 257/100.ccls. 257/101.ccls. 257/102.ccls. 257/103.ccls. "372"/\$7.ccls.) | US-PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/05/26 20:42 |

| | | | | | | |
|------|----|--|---|----|-----|---------------------|
| S200 | 38 | (planari?ation planari?e planari?ed planari?ing).ti,ab, clm. and (integrated adj circuit IC adj chip).ti,ab, clm. and (light-emitting light adj emitting laser) and (thin adj film adj transistor 257/79.ccls. 257/8\$1. ccls. 257/9\$1.ccls. 257/100.ccls. 257/101.ccls. 257/102.ccls. 257/103.ccls. "372"/\$7.ccls.) and @ack-"20031225" | US-PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/05/26 20:48 |
| S201 | 38 | (planari?ation planari?e planari?ed planari?ing).ti,ab, clm. and (integrated adj circuit IC adj chip).ti,ab, clm. and (light-emitting light adj emitting laser) and (thin adj film adj transistor 257/79.ccls. 257/8\$1. ccls. 257/9\$1.ccls. 257/100.ccls. 257/101.ccls. 257/102.ccls. 257/103.ccls. "372"/\$7.ccls.) and @ack-"20031225" and (planari?ation planari?e planari?ed planari?ing) | US-PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/05/26 20:57 |
| S202 | 2 | ("6734930").PN. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2007/05/26 20:57 |
| S203 | 1 | "5504599".PN. | USPAT; USOCR | OR | OFF | 2007/05/26 20:58 |
| S204 | 1 | "5796509".PN. | USPAT; USOCR | OR | OFF | 2007/05/26 20:59 |
| S205 | 1 | "5926239".PN. | USPAT; USOCR | OR | OFF | 2007/05/26 21:01 |
| S206 | 1 | "6194837".PN. | USPAT; USOCR | OR | OFF | 2007/05/26 21:01 |
| S207 | 1 | "6441551".PN. | USPAT; USOCR | OR | OFF | 2007/05/26 21:02 |
| S208 | 1 | "6441551".PN. | USPAT; USOCR | OR | OFF | 2007/05/26 21:03 |
| S209 | 1 | "6556260".PN. | USPAT; USOCR | OR | OFF | 2007/05/26 21:03 |

| | | | | | | |
|------|------|---|---|----|-----|---------------------|
| S210 | 1 | "6628068".PN. | USPAT; USOCR | OR | OFF | 2007/05/26 21:04 |
| S211 | 1 | "20020196387".PN. | US-PGPUB | OR | OFF | 2007/05/26 21:04 |
| S212 | 1 | "20030063231".PN. | US-PGPUB | OR | OFF | 2007/05/26 21:05 |
| S213 | 1 | "20030127656".PN. | US-PGPUB | OR | OFF | 2007/05/26 21:22 |
| S214 | 2 | ("5796509").PN. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2007/05/26 21:23 |
| S215 | 0 | S214 and (planarized planarised planarize planarise planarization planarisation) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2007/05/26 21:24 |
| S216 | 2125 | (planarized planarised planarize planarise planarization planarisation) and lod and tft | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/05/26 21:24 |
| S217 | 738 | (planarized planarised planarize planarise planarization planarisation) and (liquid adj crystal adj display lod) and (thin adj film adj transistor tft) and (planarized planarised planarize planarise planarization planarisation).ti,ab,clm. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/05/26 21:26 |
| S218 | 464 | (planarized planarised planarize planarise planarization planarisation) and (liquid adj crystal adj display lod) and (thin adj film adj transistor tft) and (planarized planarised planarize planarise planarization planarisation).ti,ab,clm. and @ad<"20031231" | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/05/26 21:27 |

| | | | | | | |
|------|-----|---|---|----|----|---------------------|
| S219 | 53 | (planarized planarised planarize planarise planarization planarisation) and ((el electroluminescent) adj (layer film)) and (thin adj film adj transistor tft) and (planarized planarised planarize planarise planarization planarisation).ti,ab,clm. and @ad<"20031231" | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/05/26 22:45 |
| S220 | 717 | (planarized planarised planarize planarise planarization planarisation) and ((el electroluminescent) adj (layer film)) and (thin adj film adj transistor tft) and (planarized planarised planarize planarise planarization planarisation)".ti,ab" and (planarized planarised planarize planarise planarization planarisation).clm. and @ad<"20031231" | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/05/26 21:35 |
| S221 | 4 | (planarized planarised planarize planarise planarization planarisation) and ((el electroluminescent) adj (layer film)) and (thin adj film adj transistor tft) and (planarized planarised planarize planarise planarization planarisation).ti,ab. and (planarized planarised planarize planarise planarization planarisation).clm. and @ad<"20031231" | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/05/26 21:35 |
| S222 | 51 | ppv near3 semiconductor | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/05/26 22:47 |
| S223 | 70 | (polyparaphenylene adj vinylene polyvinyl adj carbazole polyfluorane) near6 semiconductor | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/05/26 22:49 |
| S224 | 55 | (polyparaphenylene adj vinylene polyvinyl adj carbazole polyfluorane) near6 semiconductor | USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/05/26 22:54 |

| | | | | | | |
|------|-------|---|--|----|----|---------------------|
| S225 | 0 | (polyparaphenylene adj vinylene and polyvinyl adj carbazole and polyfluorane) near6 semiconductor | USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/05/26 22:53 |
| S226 | 6 | (polyparaphenylene adj vinylene polyvinyl adj carbazole polyfluorane) near6 semiconductor and electroluminescent | USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/05/26 23:24 |
| S227 | 6 | (polyparaphenylene adj vinylene polyvinyl adj carbazole polyfluorane) near6 (organic adj compound) and electroluminescent | USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/05/27 00:30 |
| S228 | 4021 | (planari?ation planari?e planari?ed planri?ing) near4 (semiconductor silicon) | US-PGPUB | OR | ON | 2007/05/27 10:08 |
| S229 | 12258 | (planari?ation planari?e planari?ed planri?ing) near4 (semiconductor silicon) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/05/27 10:08 |
| S230 | 4511 | (planari?ation planari?e planari?ed planari?ing) near1 (semiconductor silicon) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/05/27 10:09 |
| S231 | 0 | (planari?ation planari?e planari?ed planari?ing) near1 (semiconductor silicon) and tft and el adj (layer film) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/05/27 10:09 |

| | | | | | | |
|------|-----|---|---|----|----|---------------------|
| S232 | 7 | (planari?ation planari?e planari?ed planari?ing) near2 (semiconductor silicon) and tft and el adj (layer film) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/05/27 10:10 |
| S233 | 26 | (planari?ation planari?e planari?ed planari?ing) near3 (semiconductor silicon) and tft and el adj (layer film) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/05/27 10:14 |
| S234 | 446 | (planari?ation planari?e planari?ed planari?ing) near3 (semiconductor silicon) and tft | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/05/27 10:14 |
| S235 | 314 | (planari?ation planari?e planari?ed planari?ing) near2 (semiconductor silicon) and tft | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/05/27 10:35 |
| S236 | 18 | (planari?ation planari?e planari?ed planari?ing) near2 (semiconductor silicon) and (257/79.cds. 257/8\$1.cds. 257/9\$1.cds. 257/10\$1.cds.) and @ad<"20031231" | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/05/27 10:54 |
| S237 | 0 | "20010019133".pn. and common adj electrode | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/05/27 10:55 |

| | | | | | | |
|------|---|--|---|----|-----|---------------------|
| S238 | 2 | "20010019133".pn. and electrode | US-PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/05/27 11:15 |
| S239 | 0 | (semiconductor near 1 energy).as. and optical adj print adj head.clm. and (EL adj (layer film)) | US-PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/05/27 11:16 |
| S240 | 0 | optical adj print adj head.clm. and (EL adj (layer film)) | US-PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/05/27 11:16 |
| S241 | 2 | optical adj print adj head.ti,ab,clm. and (EL adj (layer film)) | US-PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/05/27 11:19 |
| S242 | 2 | jp-2001167874\$-\$.did. | US-PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/05/27 11:36 |
| S243 | 2 | ("6841183").PN. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2007/05/27 11:37 |

| | | | | | | |
|------|-------|--|---|----|-----|---------------------|
| S244 | 2 | ("6841813").PN. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2007/05/27 11:47 |
| S245 | 18433 | ((257/79) or (257/8\$1) or (257/9\$1) or (257/100) or (257/101) or (257/102) or (257/103) or (257/499) or (257/501) or (257/678) or (257/905) or (257/906) or (257/911)).COLS. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2007/05/27 11:52 |
| S246 | 18676 | ((257/79) or (257/8\$1) or (257/9\$1) or (257/100) or (257/101) or (257/102) or (257/103) or (257/499) or (257/501) or (257/678) or (257/905) or (257/906) or (257/911) or (257/e31.095) or (257/e31.096)).COLS. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2007/05/27 11:52 |
| S247 | 37 | S246 and (planari?e planari?ed planari?ing planari?ation) near20 (semiconductor silicon).ti,ab,clm. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/05/27 12:01 |
| S248 | 7 | (fujiwara.in. sakuta.in. abiko.in. oki adj data.as. ogihara.in.) and (planari?e planari?ed planari?ing planari?ation) near20 (semiconductor silicon).clm. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/05/27 12:11 |
| S249 | 4 | (fujiwara.in. sakuta.in. abiko.in. oki adj data.as. ogihara.in.) and (planari?e planari?ed planari?ing planari?ation) near20 (semiconductor silicon).clm. and compound adj semiconductor | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/05/27 12:41 |
| S250 | 67 | nakamura.in. and blue adj "LED" | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/05/27 12:42 |

| | | | | | | |
|------|-----|---|---|----|----|---------------------|
| S251 | 9 | nakamura.in. and blue adj "LED" and compound adj semiconductor | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/05/27 12:43 |
| S252 | 164 | nakamura.in. and GaN and compound adj semiconductor | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/05/27 12:45 |
| S253 | 4 | nakamura.in. and GaN and compound adj semiconductor and (planari?ing planari?e planari?ation) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/05/27 12:46 |
| S254 | 293 | GaN and compound adj semiconductor and (planari?ing planari?e planari?ation) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/05/27 12:53 |
| S255 | 4 | "651586".pn. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/05/27 12:54 |
| S256 | 4 | "651586".ap. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/05/27 12:54 |
| S257 | 1 | (US-20040135157-\$).did. | US-PGPUB | OR | ON | 2008/01/09 08:33 |
| S258 | 1 | (US-20040135157-\$).did. and (flat flatness plaraized planarization nanometer nm) | US-PGPUB | OR | ON | 2008/01/09 08:37 |

| | | | | | | |
|------|---|---|---|----|-----|---------------------|
| S259 | 2 | ("20010019133").PN. | US-PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2008/01/09 08:43 |
| S260 | 2 | jp-2001167874\$-\$\$.did. | US-PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/01/09 08:42 |
| S261 | 1 | S259 and (planari?ed planari?ing planari?e planari?ation) | US-PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/01/09 11:42 |
| S262 | 0 | ("298736.ap.").PN. | US-PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2008/01/09 11:42 |
| S263 | 9 | "298736".ap. | US-PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/01/09 11:49 |
| S264 | 5 | "3632470".pn. | US-PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/01/09 11:49 |

| | | | | | | |
|------|------|---|---|----|-----|---------------------|
| S265 | 2 | ("7253716").PN. | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2008/01/09 11:50 |
| S266 | 0 | ("(planarizeplanarizationplanarizing).ti,ab,clm. andflatnessnear20(nmangstrom)").PN. | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2008/01/10 11:46 |
| S267 | 62 | (planarize planarization planarizing).ti,ab,clm. and flatness near20 (nm angstrom) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/01/10 11:46 |
| S268 | 1 | (US-20040135157-\$).did. | US-PGPUB | OR | ON | 2008/01/10 11:48 |
| S269 | 1 | (US-20040135157-\$).did. and interdielectric near10 (thick thickness) | US-PGPUB | OR | ON | 2008/01/10 11:54 |
| S270 | 8 | mondtxp. | USPAT | OR | ON | 2008/01/10 13:57 |
| S271 | 4604 | pixel adj electrode and (electroluminescen\$2 EL) adj (element device) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/01/10 13:58 |

| | | | | | | |
|------|-----|--|---|----|-----|---------------------|
| S272 | 271 | pixel adj electrode and (electroluminescen\$2 EL) adj (element device) and planari?e | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/01/10 13:58 |
| S273 | 144 | flatness near10 (peak-to-valley root-mean-square rms) and (silicon semiconductor) and substrate | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/01/10 16:23 |
| S274 | 1 | (US-20040135157-\$.)did. | US-PGPUB | OR | ON | 2008/01/10 16:34 |
| S275 | 1 | (US-20040135157-\$.)did. and flatness | US-PGPUB | OR | ON | 2008/01/10 16:35 |
| S276 | 9 | (US-20050087510-\$. or US-20050051437-\$. or US- 20050009296-\$. or US-20040132253-\$. or US- 20040130775-\$. or US-20040113150-\$. or US- 20030038321-\$. or US-20030006406-\$. or US- 20020195440-\$.)did. | US-PGPUB | OR | ON | 2008/01/10 16:55 |
| S277 | 1 | (US-20040135157-\$.)did. | US-PGPUB | OR | ON | 2008/01/10 17:00 |
| S278 | 0 | (US-20040135157-\$.)did. and "entire" | US-PGPUB | OR | ON | 2008/01/10 17:00 |
| S279 | 0 | (US-20040135157-\$.)did. and ("complete" "entire") | US-PGPUB | OR | ON | 2008/01/10 17:01 |
| S280 | 0 | (US-20040135157-\$.)did. and (complete entire) | US-PGPUB | OR | ON | 2008/01/10 17:01 |
| S281 | 1 | (US-20040135157-\$.)did. and (complete entire full) | US-PGPUB | OR | ON | 2008/01/10 17:01 |
| S282 | 1 | (US-20040135157-\$.)did. and "same" near2 (thick thickness) | US-PGPUB | OR | OFF | 2008/01/11 10:38 |

| | | | | | | |
|------|-------|--|---|----|-----|---------------------|
| S283 | 12941 | ((257/79) or (257/88) or (257/93) or (257/98) or (257/99) or (257/499) or (257/501) or (257/678) or (257/905) or (257/906) or (257/911)).CCL.S. | US-PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2008/01/11 11:36 |
| S284 | 2 | S283 and (planarized planarization Planarizing planarize) and flatness near 20 (thick thickness angstrom nm) and (VLSI ULSI integrated adj circuit IC) | US-PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/01/11 11:39 |
| S285 | 2 | ("20020187650").PN. | US-PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2008/01/11 14:39 |
| S286 | 2 | ("20010019133").PN. | US-PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2008/01/11 14:57 |
| S287 | 1 | (US-20040135157-\$).did. | US-PGPUB | OR | ON | 2008/08/30 16:01 |
| S288 | 0 | ("1aninorganic").PN. | US-PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2008/08/30 16:01 |

| | | | | | | |
|------|-----|---|---|----|-----|---------------------|
| S289 | 0 | S287 and inorganic | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/08/30 16:01 |
| S290 | 2 | ("20010019133").PN. | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2008/08/30 16:09 |
| S291 | 718 | transparent near4 metal near4 pixel | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/08/30 16:10 |
| S292 | 0 | transparent near4 metal near4 pixel adj electrode and electroluminescen\$2 | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/08/30 16:11 |
| S293 | 19 | transparent near4 metal near4 pixel adj electrode and electroluminescen\$2 | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/08/30 16:11 |
| S294 | 8 | transparent near4 metal near4 pixel adj electrode and electroluminescen\$2 and @ad< "20021225" | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/08/30 16:14 |

| | | | | | | |
|------|------|---|---|----|----|---------------------|
| S295 | 1 | S287 and (metal metallic) | US-PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/08/30 16:17 |
| S296 | 9469 | (metal metallic) near4 (ito indium-tin-oxide zto zinc-tin-oxide) | US-PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/08/30 16:20 |
| S297 | 2336 | (metal metallic) near1 (ito indium-tin-oxide zto zinc-tin-oxide) | US-PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/08/30 16:20 |
| S298 | 1246 | (metal metallic) near1 (ito indium-tin-oxide zto zinc-tin-oxide) and pixel | US-PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/08/30 16:20 |
| S299 | 188 | (metal metallic) near1 (ito indium-tin-oxide zto zinc-tin-oxide) same pixel and @ad<"20021224" | US-PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/08/30 16:20 |
| S300 | 84 | (metal metallic) near1 (ito indium-tin-oxide zto zinc-tin-oxide) near6 pixel and @ad<"20021224" | US-PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/08/30 16:21 |

| | | | | | | |
|------|-----|---|---|----|----|---------------------|
| S301 | 94 | organic adj semiconductor adj compound and @ad<"20021224" | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/08/30 19:43 |
| S302 | 12 | organic adj semiconductor adj compound.ti. and @ad<"20021224" | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/08/30 19:43 |
| S303 | 14 | organic adj semiconductor adj compound.ti,ab,clm. and transistor and @ad<"20021224" | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/08/30 19:44 |
| S304 | 184 | (planari?ation planari?e\$1 planari?ing) and transistor and (peak-to-valley roughness flatness atomically adj flat) near4 ("10" adj nm "5" adj nm "1" adj nm) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/08/30 19:51 |
| S305 | 36 | (planari?ation planari?e\$1 planari?ing) and transistor and (peak-to-valley roughness flatness atomically adj flat) near4 ("10" adj nm "5" adj nm "1" adj nm) and @ad<"20021224" | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/08/30 19:52 |
| S306 | 9 | (planari?ation planari?e\$1 planari?ing).ti,ab,clm. and transistor and (peak-to-valley roughness flatness atomically adj flat) near4 ("10" adj nm "5" adj nm "1" adj nm) and @ad<"20021224" | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/08/30 19:55 |

| | | | | | | |
|------|---|---|---|----|-----|---------------------|
| S307 | 0 | (planari?ation planari?e\$1 planari?ing).ti,ab,dlm. and transistor and (peak-to-valley roughness flatness atomically adj flat) near4 ("10" adj nm "5" adj nm "1" adj nm) and @ad<"20021224" and (light-emitting ligh adj emitting) | US-PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/08/30 20:04 |
| S308 | 1 | (planari?ation planari?e\$1 planari?ing).ti,ab,dlm. and transistor and (peak-to-valley roughness flatness atomically adj flat) near4 ("10" adj nm "5" adj nm "1" adj nm) and @ad<"20021224" and (light-emitting light adj emitting) | US-PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/08/30 20:04 |
| S309 | 1 | (planari?ation planari?e\$1 planari?ing).ti,ab,dlm. and transistor and (peak-to-valley roughness flatness atomically adj flat) near4 ("10" adj nm "5" adj nm "1" adj nm) and @ad<"20021224" and (light-emitting light adj emitting) and oxide adj cap | US-PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/08/30 20:25 |
| S310 | 1 | (US-20040135157-\$.)did. | US-PGPUB | OR | ON | 2008/08/30 20:41 |
| S311 | 1 | (US-20040135157-\$.)did. and edge | US-PGPUB | OR | ON | 2008/08/30 20:42 |
| S312 | 0 | "6242324".pn. and (planarize planarizing planarization) | US-PGPUB | OR | OFF | 2008/08/31 09:13 |
| S313 | 0 | "6242324".pn. and (planarize planarizing planarization) | US-PGPUB | OR | ON | 2008/08/31 09:13 |
| S314 | 0 | "6242324".pn. | US-PGPUB | OR | ON | 2008/08/31 09:13 |
| S315 | 2 | ("6242324").PN. | US-PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2008/08/31 09:14 |

| | | | | | | |
|------|---|---|---|----|----|---------------------|
| S316 | 1 | S315 and (planarize planarized planarization planarizing) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/08/31 09:14 |
|------|---|---|---|----|----|---------------------|

8/31/2008 3:52:23 PM

C:\Documents and Settings\jmond\My Documents\EAST\Workspaces\10743104.wsp